Serial-kinematic monolithic nanopositioner with in-plane bender actuators

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A R T I C L E   I N F O

Keywords:
- Nanopositioning
- Atomic force microscopy
- Piezoelectric actuators

A B S T R A C T

This article describes a monolithic nanopositioner constructed from in-plane bending actuators which provide greater deflection than previously reported extension actuators, at the expense of stiffness and resonance frequency. The proposed actuators are demonstrated by constructing an XY nanopositioning stage with a serial kinematic design. Analytical modeling and finite-element-analysis accurately predicts the experimental performance of the nanopositioner. A 10 μm range is achieved in the X and Y axes with an applied voltage of ±/200 V. The first resonance mode occurs at 250 Hz in the Z axis. The stage is demonstrated for atomic force microscopy imaging.

1. Introduction

Nanopositioning devices are a class of short-range motion stages with resolution on the nanometer scale or below [1]. Applications include atomic force microscopy [2–8], data storage [9], nanofabrication [10,11], cell surgery [12], and precision optics [13].

Piezoelectric tube scanners were the first common nanopositioning systems used in Atomic Force Microscopy (AFM) [14]. Since these are constructed from a single piece of piezoelectric ceramic, they are known as monolithic structures which provide both actuation and some motion guidance [15,16]. The travel range of piezoelectric tubes is determined by the length, radius, and tube wall thickness. They tend to be long (e.g. 50 mm) and thin (e.g. 7 mm diameter) which can be difficult to integrate due the significant vertical height. There is significant scope to explore other monolithic geometries that are similar in cost but provide improved performance and alternative dimensions.

The most common class of nanopositioners are flexure-based devices [17–25]. In these designs, metal flexures guide a central stage which is driven by piezoelectric stack actuators. Metal flexure-based nanopositioners provide the highest performance metrics with respect to displacement gain, resonance frequency, cross-coupling, and load size. However, they are also much larger, heavier, and more costly than monolithic devices like piezoelectric tubes. In addition, assembling and preloading piezoelectric stack actuators are required to avoid damage to the stack actuators [26]. Preload mechanisms require careful design considerations and precise machining which increase manufacturing time and cost.

There is significant demand for low profile positioning systems in applications such as optical microscopy [27], atomic force microscopy [28], and in particular, scanning electron microscopy (SPM) where the load-lock area is typically less than 10 mm in height [29,30]. Products designed for these applications include the SuperFlat AFM from Kleindiek nanotechnik [28], the P-541 and P-542 Series from Physik Instrumente [31], and the Nano-Bio and Nano-LPS Series from Mad City Labs [27].

This work combines monolithic and flexure-based design approaches which results in a vertical thickness of less than 1 mm, which is an order of magnitude less than current metal flexure based devices. The advantages of the proposed approach over metal flexure designs are generalized by lower vertical height; lower mass; no preload mechanism; compatibility with vacuum and low temperature applications. The proposed method is light weight, which makes it suitable for applications such as camera stabilization and optical scanning from small-scale air vehicles [32]. The simple mechanical structure of the proposed method also avoids the need for stack actuators and the resulting preloading requirements. Since bonding or encapsulation materials are not required, the reported monolithic design can also be easily adapted to high-vacuum and cryogenic applications.

The disadvantages of the proposed method stem from the low vertical height that results in low vertical stiffness. This results in higher vertical cross-coupling and a lower payload capability compared to metal flexure devices. The most useful range of payload masses for the proposed method is less than 10 g.

Microelectromechanical systems (MEMs) are another class of monolithic flexure-based nanopositioners [33]. These devices provide the

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A comparison of monolithic extension actuators [41] and the in-plane bending actuators described in this work. $L$ is the beam length, $t_y$ is the width, and $\propto$ means proportional to.

<table>
<thead>
<tr>
<th>Actuator type</th>
<th>Extension [41]</th>
<th>In-plane bender</th>
</tr>
</thead>
<tbody>
<tr>
<td>Deflection</td>
<td>$\propto L$</td>
<td>$\propto L^2/t_y$</td>
</tr>
<tr>
<td>In-plane stiffness</td>
<td>$\propto t_y/L$</td>
<td>$\propto t_y/L^2$</td>
</tr>
<tr>
<td>Out-of-plane stiffness</td>
<td>Similar</td>
<td>Similar</td>
</tr>
<tr>
<td>Best suited to</td>
<td>Parallel kinematic</td>
<td>Serial kinematic</td>
</tr>
</tbody>
</table>
The nanopositioner design. (a) The photo of the prototype design. (b) Schematic with the structural dimensions. (c) Schematic of the piezoelectric electrode layout.

Fig. 3. Each active flexure has four electrodes, one on each quarter of the flexure in the X–Y plane. Two of the electrodes are actuated positively and the other two are actuated negatively. The diagram shows the positive orientation of the deflection \( w_0(x) \), rotation \( w'_0(x) \), and the four degrees-of-freedom \((w_1, \theta_1, w_2, \theta_2)\) of the reduced order model.

allows a direct performance comparison. The number of flexures were chosen to maximize the stiffness given the available space. The number of parallel flexures does not affect the travel range, but the number is proportional to stiffness, so the number should be maximized. The other trade-offs between the dimensions and performance are summarized in Table 1.

The motion of the X and Y axes are constrained by a set of thick flexures on either side of the stage. The flexures guide the nanopositioner in the compliant directions, and provide the mechanism for actuation. The inner X axis is guided by four active flexures and two non-active flexures. The outer Y axis is guided by 20 active flexures.

The electrode over each active flexure is split into four quadrants as shown in Fig. 3. Diagonally opposite quadrants are electrically connected. With the bottom electrode grounded, opposite voltages are applied to the two electrode sections to create side-to-side motions. When actuators of a single axis are moved in the same direction, translational motions are generated. When they are moved in opposing directions, rotational motion is generated. The electrode arrangement of the complete nanopositioner is shown in Fig. 2(c). The electrode sections on each axis are driven with opposite polarity voltages, where Sections 1 and 2 develop motion in the Y axis and Sections 3 and 4 develop motion in the X axis.

The nanopositioner is mounted onto a metal frame, as shown in Fig. 2(a), with the grounded electrode facing upward. This prevents access to the high voltage electrodes on the opposite side for the safety of the user and protection of the sample and equipment interacting with the device.

3. Electromechanical model of an active flexure

To analyze the dynamics of the piezoelectric nanopositioner, a model of a single piezoelectric flexure, shown in Fig. 3, is derived. The constitutive equations of the piezoelectric material, Euler–Bernoulli beam theory, and Hamilton’s principle are applied to relates the stress, strain, electric field, and electric displacement in the structure. This results in a voltage-deflection model of the active flexure.

3.1. Stress–displacement relationship

Euler–Bernoulli beam theory parameterizes the 3-dimensional displacement field in the structure in terms of the 1-dimensional deflection of the flexure \( u_0 \) \[43–45\],

\[
u_1(x, y, z) = -yu'_0(x), \quad (1)
\]
\[ u_2(x, y, z) = u_0(x), \] (2)
\[ u_3(x, y, z) = 0, \] (3)

where \((u_1, u_2, u_3)\) is the displacement of an infinitesimal piece of the flexure in the X, Y, and Z axes respectively, and the prime (') is the derivative with respect to \(x\). \(u_0\) is the angle of rotation of the flexure around the neutral axis as shown in Fig. 3. The displacement field indicates that: the displacement in the Y axis is solely due to the deflection of the flexure; there is no displacement in the Z axis; and displacement in the X axis is due to the cross-sectional rotation of the flexure. With the above displacement field, there is only one non-zero component of the strain, that is,
\[ S_1(x, y, z) = u'_1 = -yu_0'' \] (4)

3.2. Electric field–voltage relationship

A parallel-plate capacitative structure is used to model the generated electric field. One-side of the flexure is grounded, and the other is split into four electrodes distributed in the XY-plane. The piezoelectric flexure is polarized along the Z axis. The electric field is,
\[ E_3(x, y, z) = -B_3(x, y)V_e \] (5)
where \(V_e\) is the magnitude of the input voltage and \(B_3\) models the geometry of the electrodes,
\[ B_3(x, y) = \frac{1}{t_z} \begin{cases} -1 & x < L/2, \ y > 0 \\ 1 & x < L/2, \ y < 0 \\ 1 & x > L/2, \ y > 0 \\ -1 & x > L/2, \ y < 0 \end{cases} \] (6)
where \(t_z\) is the thickness of the flexure in the Z direction.

3.3. Constitutive equations

An Euler–Bernoulli beam has only one non-zero stress and strain component, and the electric field is only applied in the polarization direction of the piezoelectric material. In this case, the constitutive equations simplify to
\[ T_1 = c_{11}S_1 - e_{31}E_3, \] (7)
\[ D_3 = e_{31}S_3 + \epsilon_{33}E_3, \] (8)
where \(T_1\) is the stress, \(D_3\) is the electric displacement, \(c_{11}\) is Young’s modulus, \(e_{31}\) is the piezoelectric coefficient, and \(\epsilon_{33}\) is the permittivity.

3.4. Discretization of the model

To simplify the model, deflections of the flexure are parameterized by four degrees-of-freedom (DOFs), which are the deflections \((u_1, u_2, w_1, w_2)\) and rotations \((\theta_1, \theta_2)\) at both ends of the flexure as shown in Fig. 3. To form the reduced-order model of the flexure, the deflection is expressed as
\[ u_0(x) = N_e(x)d_e, \] (9)
where \(N_e\) is a vector of interpolation functions and \(d_e\) is a vector of the DOFs,
\[ d_e = [u_1, \theta_1, w_1, \theta_2]^T. \] (10)
The interpolation functions are the Hermite cubic splines given by [46],
\[ N_e(x) = \begin{bmatrix} N_0(x) & N_2(x) & N_3(x) & N_4(x) \end{bmatrix}, \] (11)
where,
\[ N_0(x) = 1 - \frac{3x^2}{L^2} + \frac{x^3}{L^2}, \] (12)
\[ N_2(x) = L \left( \frac{x}{L} - \frac{2x^3}{3L^3} + \frac{x^2}{L^2} \right), \] (13)
\[ N_3(x) = \frac{3x^2}{L^2} - \frac{2x^3}{3L^3}. \] (14)
\[ N_4(x) = L \left( -\frac{x^2}{L^2} + \frac{x^3}{L^3} \right). \] (15)

For the development of the model, the strain \(S_1\) is expressed in terms of \(d_e\) by substituting Eq. (9) into Eq. (4), which gives,
\[ S_1 = -yN''_0(x)d_e = B_3(x, y)d_e. \] (16)

3.5. The governing differential equation

Hamilton’s principle is the fundamental physical principle used to derive the governing differential equations of the piezoelectric flexure. It is mathematically stated as [44,45,47],
\[ 0 = \delta \int \left[ T - H \right] dt, \] (17)
where \(H\) is the enthalpy of the piezoelectric flexure, \(T\) is the kinetic energy, \(\delta\) is the variational operator, and \((t_1, t_2)\) is an arbitrary time interval. The expressions for the enthalpy and kinetic energy are,
\[ H = \frac{1}{2} \int_{t_1}^{t_2} T_1 S_1 - D_3 E_3 \ d\Omega, \] (18)
\[ T = \frac{1}{2} \int_{\Omega} \rho \left( u_1'^2 + u_2'^2 + w_1'^2 \right) \ d\Omega, \] (19)
where the domain over the volume of the flexure is
\[ \Omega = \{(x, y, z) : x \in [0, L], y \in [-\frac{L}{2}, \frac{L}{2}], z \in [0, t_z]\}. \] (20)
and \(\rho\) is the material density. The constitutive equation from Eq. (7) and the model discretization from Eqs. (5), (9) and (16) are substituted into the above energy expressions. Note that in Euler–Bernoulli beam theory the rotary inertia is assumed to have a negligible contribution to the kinetic energy and is ignored [48]. In terms of the discretized parameters \(V_e\) and \(d_e\), the energy expressions are
\[ H = \frac{1}{2} \frac{d_t^T}{2} K_e d_e + \frac{d_t^T}{2} P_e V_e - \frac{1}{2} \int_{\Omega} \epsilon_{33}(B_3 V_e)^2 \ d\Omega, \] (21)
\[ T = \frac{1}{2} d_t^T M_e d_e, \] (22)
where the parameters \(M_e, K_e,\) and \(P_e\) are,
\[ M_e = \int_{\Omega} \rho N_t^T N_e \ d\Omega, \] (23)
\[ K_e = \int_{\Omega} c_{11} N_t^T B_3 \ d\Omega, \] (24)
\[ P_e = \int_{\Omega} e_{33} N_t^T B_3 \ d\Omega. \] (25)
Substituting Eqs. (21) and (22) into Eq. (17) and evaluating Hamilton’s principle results in the reduced-order differential equation that governs the dynamics of the piezoelectric flexure,
\[ M_e d_t + K_e d_e + P_e V_e = 0. \] (26)
Eqs. (23)–(25) for the mass, stiffness, and piezoelectric matrices of the reduced-order model are evaluated as,
\[ K_e = \frac{c_{11} L}{6} \begin{bmatrix} 12 & 64 & -12 & 64 & -12 & 64 \\ 64 & 42 & -64 & 42 & -64 & 42 \\ -12 & -64 & 12 & -64 & 12 & -64 \\ 64 & 42 & -64 & 42 & -64 & 42 \\ -12 & -64 & 12 & -64 & 12 & -64 \\ 64 & 42 & -64 & 42 & -64 & 42 \end{bmatrix}, \] (28)
\[ P_e = \frac{e_{33} L}{8L} \begin{bmatrix} -6 & -3L & 6 & -3L \end{bmatrix}^T, \] (29)
where the area \(A\) and moment of inertia \(I\) are,
\[ A = t_1 t_2, \] (30)
\[ I = \frac{t_1^3 t_2}{12}. \] (31)
4. Electromechanical model of the piezoelectric nanosizer

In Section 4.1, the out-of-plane resonance frequencies are derived using a combination of the flexure models from Section 3 with the corresponding thickness and width parameters for bending in the out-of-plane direction. In addition, since there is no actuation in the out-of-plane direction, the piezoelectric constant can be set to zero. Section 4.2 combines a set of piezoelectric flexure models derived in Section 3 with appropriate boundary conditions to derive the in-plane displacement per volt.

4.1. Static modeling

The static deflection of the nanopositioner is derived by assuming the moving platform is rigid and the flexures are constrained with a fixed-guided configuration. The displacement of the inner axis is defined as \( q_i \), and the displacement of the outer axis is \( q_o \). With the fixed-guided configuration of each flexure, the rotations \( \theta_i \) and \( \theta_j \), and the deflection at the fixed-end \( u_j \), are therefore zero. The displacement at the guided end is equal to either \( q_i \) or \( q_o \). As a result, \( d_i \) of each flexure is expressed as,

\[
\begin{align*}
d_i &= T_f q_i & \text{for inner axis flexures} \\
T_f &= \begin{bmatrix} 0 & 1 \\
1 & 0 \\
0 & 0 \\
1 & 0 \
\end{bmatrix} & \text{for outer axis flexures}
\end{align*}
\]

Next, the model in Eq. (32) for each flexure is assembled into a single system for each axis. For the inner-axis, the static model is

\[
0 = n_i T_f^T K_f T_f q_i + n_i T_f^T P_f V_i, \quad (34)
\]

\[
= 12 \varepsilon_{ij} (n_i I + \tilde{h}_i I) q_i + n_i \frac{3 \varepsilon_{ij} I}{4L} V_i, \quad (35)
\]

where \( n_i \) is the number of active flexures connected to the stage, and \( V_i \) is the inner-axis input voltage. In addition, there are two smaller flexures connected to the inner stage which are passive. Their number, thickness, moment of inertia, and stiffness matrix are designated as \( n_j \), \( \tilde{h}_j \), \( I \), and \( K_f \), respectively. With the parameters in Table 2 the gain of the inner axis \( q_i/V_i \) is calculated to be 14.73 nm V\(^{-1}\), which agrees with the FEA and experimental results summarized in Table 6.

Table 2

<table>
<thead>
<tr>
<th>Description</th>
<th>Parameter</th>
<th>Value</th>
</tr>
</thead>
<tbody>
<tr>
<td>Flexure length (mm)</td>
<td>( L )</td>
<td>17.5</td>
</tr>
<tr>
<td>In-plane flexure thickness (mm)</td>
<td>( t_i )</td>
<td>5</td>
</tr>
<tr>
<td>In-plane small flexure thickness (mm)</td>
<td>( t_s )</td>
<td>2</td>
</tr>
<tr>
<td>Out-of-plane flexure thickness (mm)</td>
<td>( t_o )</td>
<td>0.5</td>
</tr>
<tr>
<td>Elastic modulus (GPa)</td>
<td>( c_{ij} )</td>
<td>66</td>
</tr>
<tr>
<td>Density (kg/m(^3))</td>
<td>( \rho )</td>
<td>7800</td>
</tr>
<tr>
<td>Piezoelectric coefficient (C/m(^2))</td>
<td>( \varepsilon_{ij} )</td>
<td>-10.92</td>
</tr>
<tr>
<td>Number of inner stage flexures</td>
<td>( n_i )</td>
<td>4</td>
</tr>
<tr>
<td>Number of small inner stage flexures</td>
<td>( n_s )</td>
<td>2</td>
</tr>
<tr>
<td>Number of outer stage flexures</td>
<td>( n_o )</td>
<td>20</td>
</tr>
</tbody>
</table>

Table 3

<table>
<thead>
<tr>
<th>Description</th>
<th>Parameter</th>
<th>Value</th>
</tr>
</thead>
<tbody>
<tr>
<td>Outer-axis effective length</td>
<td>( L_1 )</td>
<td>17.5 mm</td>
</tr>
<tr>
<td>Outer-axis effective width</td>
<td>( t_1 )</td>
<td>50 mm</td>
</tr>
<tr>
<td>Inner-axis effective length</td>
<td>( L_2 )</td>
<td>24.5 mm</td>
</tr>
<tr>
<td>Inner-axis effective width</td>
<td>( t_2 )</td>
<td>12 mm</td>
</tr>
</tbody>
</table>

Fig. 4. The out-of-plane motion is modeled by four segments. The rectangular frame that couples the inner and outer axes is modeled as a hinge. The degrees-of-freedom of the reduced-order model are label.

For the outer-axis, the static model is,

\[
0 = n_o T_f^T K_f T_f q_o + n_o T_f^T P_f V_o \quad (36)
\]

\[
= n_o \frac{12 \varepsilon_{ij} I}{L} q_o + n_o \frac{3 \varepsilon_{ij} I}{4L} V_o
\]

where \( n_o \) is the number of flexures connected to the outer-axis, and \( V_o \) is the outer-axis input voltage. The gain of the outer-axis with the parameters listed in Table 2 is 15.20 nm V\(^{-1}\), which agrees with the FEA and experimental results summarized in Table 6.

4.2. Dynamic modeling

The first modal frequency of the nanopositioner is an out-of-plane mode. Its frequency is important as it limits the speed at which the nanosizer can be operated. A reduced-order model is developed to estimate the first out-of-plane resonance frequency. The out-of-plane motion of the serial kinematic stage is modeled by four segments as shown in Fig. 4. The segments are labeled A through to D. Segments A and D model the action of the outer-axis flexures and segments B and C model the action of the inner-axis flexures. The rectangular frame that couples the inner and outer axes is modeled as a hinge to account for its compliant nature. The effective width and length of each segment is listed in Table 3. The effective length of the inner-axis is extended to account for the compliant nature of the inner-axis stage. For out-of-plane motion the moment of inertia is \( I = I_{ij}/12 \).

(26) is used to describe each beam segment in the out-of-plane model. The resulting assembled system has eight degree-of-freedom, with the DOFs labeled in Fig. 4. \( u_i \) and \( u_o \) are deflections of the rectangular frame. \( u_j, u_3, u_4, u_5 \), and \( u_6 \) are the rotations at the rectangular frame. The deflection and rotation of the inner-axis stage are defined as \( u_i \) and \( u_j \), respectively. Due to symmetry, kinematic constraints \( u_i = u_o \), \( u_2 = -u_3 \), \( u_4 = -u_5 \), and \( u_6 = 0 \) are defined. The resulting four degree-of-freedom system is,

\[
M \dot{u} + K \dot{u} = 0, \quad (38)
\]

\[
M = \begin{bmatrix}
26 A_L L_1 + A_s L_2 & -11 A_L L_3 \rho & 11 A_L L_4 \rho & 9 A_L L_5 \rho \\
-11 A_L L_3 \rho & 2 A_L L_3 \rho & 105 & -35 \\
105 & 2 A_L L_3 \rho & 210 & -35 \\
9 A_L L_5 \rho & 105 & 210 & 105
\end{bmatrix}
\]

(39)
that is \( q \) the first resonance frequency, the motion of the system is parameterized by a concise analytical expression relating the design parameters to the effects of the design parameters on the resonance frequency. To provide a point mass at the center of the nanopositioner was added to the system.

Masses placed on the nanopositioner reduce the resonance frequency. The mode shape is:

\[
\mathbf{u}_z = \begin{bmatrix} u_1 & u_2 & u_3 & u_4 \end{bmatrix}^T,
\]

where \((L_1, I_1, A_1)\) are parameters of the outer-axis and \((L_2, I_2, A_2)\) are parameters of the inner-axis. The resonance frequencies of the system in Eq. (38) are evaluated with the eigenvalue problem,

\[
\mathbf{K}_z = \omega_z^2 \mathbf{M}_z \mathbf{U}_z = 0,
\]

where \(\mathbf{U}_z\) is the mode shape and \(\omega_z\) is the resonance frequency. The solution of the eigenvalue problem using the parameters in Table 3 gives a resonance frequency of \(\omega_z = 1604.5\ \text{rad s}^{-1} \approx 255.2\ \text{Hz}\), which agrees with the FEA and experimental results summarized in Table 6. The mode shape is,

\[
\mathbf{U}_z = \begin{bmatrix} 2.006 \times 10^{-1} & 1.704 \times 10^{-1} & 9.852 \times 10^{-2} & 1.733 \times 10^{-2} \end{bmatrix}^T.
\]

Masses placed on the nanopositioner reduce the resonance frequency. A point mass at the center of the nanopositioner was added to the four-DOF model and the resulting change in resonance frequency with respect to mass is shown in Fig. 5.

The above four-DOF system is suited for fast numerical design optimization, but does not provide intuitive insight into the direct effects of the design parameters on the resonance frequency. To provide a concise analytical expression relating the design parameters to the first resonance frequency, the motion of the system is parameterized by a single DOF \(q_t\). The DOFs \(u_i\) are constrained by the mode shape, that is \(u_i = U_i q_t\), and the system in (38) becomes,

\[
\mathbf{U}_z^T \mathbf{M}_z \mathbf{U}_z \ddot{q}_t + \mathbf{U}_z^T \mathbf{K}_z \mathbf{U}_z q_t = 0.
\]

The resonance frequency of the one DOF system is,

\[
\omega_t^2 = \frac{\mathbf{U}_z^T \mathbf{K}_z \mathbf{U}_z}{\mathbf{U}_z^T \mathbf{M}_z \mathbf{U}_z}.
\]

To assess the validity of the above simplification, 1000 random mechanical systems were compared with up to 20% variation of the model parameters. The resonance frequencies predicted by both methods are plotted in Fig. 6. The one-DOF approximation is observed to overestimate the resonance frequency. However, the accuracy is considered to be acceptable for the purposes of design optimization.

For the chosen stage geometry, the analytical resonance frequencies are 8321 Hz in the X-axis, and 8986 Hz in the Y-axis, which are compared to the FEA and experimental results in Table 6. The analytical values are higher than the measured resonance frequencies; however, this was expected due to the required simplifications. It should be noted that the lateral resonance modes have a negligible effect on performance since they occur at much higher frequencies than the vertical resonance modes. That is, in the majority of applications, the vertical resonance mode will be the limiting factor.

5. Finite-element modeling

A numerical finite-element-analysis (FEA) model of the monolithic stage was constructed using ANSYS workbench. The displacement of all four edges are fixed as shown in Fig. 7. The piezoelectric properties of the stage are modeled using the ANSYS Piezo and MEMS Application Customization Toolkit (ACT) extension. The piezoelectric properties for PZT-5 A are listed in Table 4. Each piezoelectric layer is polarized outwards along its thickness direction.

To obtain the displacement per unit voltage along the X and Y axes, \(+1\ V\) and \(-1\ V\) is applied to the electrodes in orange and blue, respectively as shown in Fig. 7. The corresponding displacement is shown in the same figure. The static gain of the inner x-axis and outer x-axis is shown in the same figure. The static gain of the inner x-axis and outer x-axis is compared to the FEA and experimental results in Table 6.
Fig. 8. Simulated resonance frequencies of the serial-kinematic planar stage. The displacements are normalized and exaggerated for display purposes.

(a) First mode: 249 Hz  
(b) Second mode: 388.6 Hz

(c) Third mode: 547.9 Hz  
(d) Fourth mode: 564.4 Hz

(e) Lateral mode along the x-axis: 5243.5 Hz  
(f) Lateral mode along the y-axis: 5225.2 Hz

The resonance frequencies of the stage were simulated using the modal analysis module of ANSYS. The first four modes are shown in Fig. 8(a)–(d). The first resonant mode is the out-of-plane mode along

y-axis is 18.6 nm/V and 18.1 nm/V respectively, which agree with the experimental results summarized in Table 6.

The resonance frequencies of the stage were simulated using the modal analysis module of ANSYS. The first four modes are shown in Fig. 8(a)–(d). The first resonant mode is the out-of-plane mode along

Fig. 9. The nanopositioner is driven by a high-voltage amplifier that provides the required voltages to the four sets of electrodes for in-plane actuation.

(a) Displacement under X-Axis Actuation

(b) Displacement under Y-Axis Actuation

(c) Nanopositioner Hysteresis.

Fig. 10. The displacement of the nanopositioner.
the Z-axis which appears at 249 Hz. The analytical model closely predicts this value with 255 Hz. To search for the lateral modes along the X and Y axes of the stage, the out-of-plane motions along the Z-axis were constrained. Fig. 8(e) and (f) show the lateral modes of the stage. The lateral resonance frequencies appear at 5243.3 Hz and 5225.2 Hz along the X and Y axes respectively, which are about 12% higher than the experimental results summarized in Table 6. The discrepancy is thought to be due to the soft boundary condition in the experimental system created by the adhesive mounting layer.

If higher out-of-plane resonance frequencies are required, the thickness can be increased. However, this will require proportionally higher actuation voltage, or multiple layers. Both options result in increased complexity and cost; however, these options may be desirable in applications where the out-of-plane resonance frequency should be maximized.

The harmonic response analysis module in ANSYS was used to simulate frequency responses of the stage. A damping ratio of 0.02 was applied to the model. A sinusoidal input within a bandwidth of 10 Hz to 6500 Hz was applied to the electrodes and the corresponding displacements of the central platform were recorded to construct the frequency responses shown in Fig. 11. FEA and experimental results are discussed in the next section.

6. Experimental characterization of the nanopositioner

This section presents the experimental identification and characterization of the sensitivity, range, cross-coupling, nonlinearity, and modal responses of the nanopositioner. Fig. 9 shows the experimental setup used to drive the piezoelectric bender actuators. A custom built amplifier with two input channels \(V_x, V_y\) and four output channels \(+V_x, -V_x, +V_y, -V_y\) provides the required voltages to actuate the device. To avoid de-polarization of the piezoelectric ceramic, the applied voltages are constrained to within ±200 V.

To characterize the sensitivity of each axis and the cross-coupling between axes, a single axis is driven with a 10 Hz sinusoidal voltage with the maximum 200 V amplitude. The resulting displacement of the nanopositioner, measured with an Attocube FPS3010 interferometer, is shown in Fig. 10(a–b). The peak-to-peak travel range was 10.08 μm in the X-axis and 10.45 μm in the Y-axis. The corresponding sensitivities of the X and Y axes are 25.2 nm/V and 26.1 nm/V respectively. These values are greater than the predicted values from the FEA of 18.6 nm/V and 18.1 nm/V. The discrepancy is attributed to the voltage dependence of the piezoelectric coefficient \(e_{31}\) which is measured under small signal conditions. With large signals, which are of interest in this work, the sensitivity of soft piezoceramics is known to increase by up to a factor of two \[49\].

The hysteresis of the stage is plotted in Fig. 10(c). The maximum difference between the upward and downward paths is 14% of the full-scale deflection, which is typical of PZT-5 A material. The stage also exhibits a creep of 13% after a period of 10 min, which is also typical of PZT-SA \[50\]. These non-linearities highlight the need for closed-loop control which will be addressed in future work.

The cross-coupling exhibited by the nanopositioner is listed in Table 5. There is significant cross-coupling between the X and Y axes, and the Z axis due to the low out-of-plane stiffness. However, it should be noted that the cross-coupling is highly linear and can therefore be effectively compensated by linear inversion methods, as demonstrated in \[38\]. In AFM applications, X→Y cross-coupling rotates the image, while the X→Z cross-coupling introduces a sloping plane artifact, both of which are routinely removed by image processing.

The frequency responses in Fig. 11 were measured with a Polytec MSA-100-3D laser vibrometer. The X and Y-axis resonances are observed near 5 kHz which agree with the FEA results. A number of resonances are observed in the Z-axis motion due to the low stiffness in this axis. The four large peaks with Y-axis excitation occur at 250 Hz,
Fig. 12. The measured mode shapes of the nanopositioner by exciting the outer Y-axis and measuring the motion over the entire piezoelectric structure with the Polytec MSA-100-3D laser vibrometer.

405 Hz, 556 Hz, and 570 Hz, which correspond to the four modes predicted by the FEA model. These four mode shapes are experimentally confirmed in Fig. 12 and are significantly larger with Y-axis actuation. A set of small low frequency modes are also observed in the Z-axis which are attributed to the resonance of the wires attached to the electrodes and the dynamics from the metal frame.

The experimental results for sensitivity and resonance frequency are compared to analytical and FEA predictions in Table 6.

The resolution of the nanopositioner can be measured directly [51] or predicted from the system noise processes [52]. In this work, the output noise density of the voltage amplifier is 1.25 μV/√Hz; therefore, the standard deviation of the positioning noise can be determined from the experimental frequency responses using Eq.3 in [51]. The standard deviation of the open-loop positioning noise is 9.0 nm in the X-axis, and 8.6 nm in the Y-axis. The slightly higher noise in the X-axis is due to the higher bandwidth in this axis. Improvements to the positioning resolution could be achieved by using a lower noise amplifier, or by using sensor-based feedback control to damp the resonances, which contribute strongly to the positioning noise [52].

7. AFM imaging

The proposed monolithic nanopositioning stage was used to scan a sample underneath a Nanosurf Atomic Force Microscope (AFM), as shown in Fig. 13. A 10 μm × 10 μm area of a BudgetSensors HS-100MG calibration grating was imaged in constant-force contact-mode with a resolution of 200 × 200 pixels. With the sample placed on the central platform of the nanopositioner, Fig. 14 (Left) shows an image captured using a 1 Hz scan rate. Image artifacts caused by hysteresis and cross-coupling can be observed.

An additional scan with a line-rate of 595 Hz is shown on the right of Fig. 14. This demonstrates a useful technique for high-speed AFM where a sinusoidal scan frequency is chosen at a minima of the X→Z response [6,53,54]. In this case, a minima is observed in Fig. 11 at approximately 600 Hz. When the sample is mounted on the stage, this frequency reduces to 595 Hz. A vibration-free image can be observed in Fig. 14 (right). The method is only applicable at a discrete set of frequencies where a zero in the response exists; however, it allows a much higher scan-rate than would normally be achievable from a system with a 250 Hz first resonance frequency.

Second, the scanning frequency was selected whereby the cross-coupling from the X to the Z axis is minimal. In Fig. 11, a zero in the X→Z frequency response is observed just above 600 Hz. When the sample is placed on the stage, the increased mass reduces this zero to 595 Hz and a scan is performed at this frequency. Fig. 14 (right) shows an accurate, vibration free scan of a calibration grating using the 595 Hz scan rate which validates this approach. Image artifacts caused by non-linear hysteresis can be observed in the images.

8. Conclusions

This article describes the mechanics of a piezoelectric in-plane bender actuator. A serial-kinematic approach is then used to construct...
References


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